



TIGER ELECTRONIC CO.,LTD

SOT-89 Plastic-Encapsulate Transistors

MCK 100- 6, - 8 Silicon Planar PNP Thyristor

FEATURES

Current- I_{GT} : 200 μ A

I_{TRMS} : 0.8 A

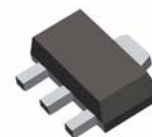
V_{DRM} : MCK100-6: 400 V

MCK100-8: 600 V

Operating and storage junction temperature range

T_J , T_{stg} : -55°C to +150°C

SOT-89



1.KATHODE

2.ANODE

3.GATE

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol		Test conditions	MIN	MAX	UNIT
On state voltage *	V_{TM}		$I_{TM}=1\text{A}$		1.7	V
Gate trigger voltage	V_{GT}		$V_{AK}=7\text{V}$		0.8	V
Peak Repetitive forward and reverse blocking voltage MCK100-6 MCK100-8	V_{DRM} AND V_{RRM}		$I_{DRM}=10\text{ }\mu\text{A}$, $V_{MAX}=1010\text{ V}$	400 600		V
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}		$V_{AK}=\text{Rated}$ V_{DRM} or V_{RRM}		10	μA
Holding current	I_H		$I_{HL}=20\text{ mA}$, $A_v=7\text{ V}$		5	mA
Gate trigger current	I_{GT}	A2	$V_{AK}=7\text{V}$	5	15	μA
		A1		15	30	μA
		A		30	80	μA
		B		80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.

Typical Characteristics

MCK100-6,-8

FIGURE 1 – MCR100-8 CURRENT DERATING
(REFERENCE: CASE TEMPERATURE)

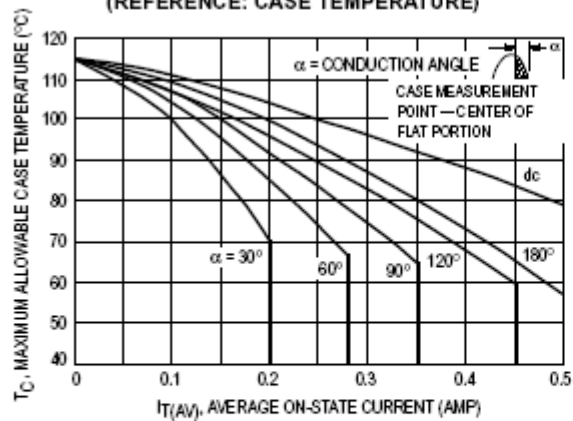


FIGURE 2 – MCR100-8 CURRENT DERATING
(REFERENCE: AMBIENT TEMPERATURE)

